

TMUX621x 具有 1.8V 逻辑的 36V、低 Ron、1:1 (SPST)、4 通道精密开关

1 特性

- 双电源电压范围：±4.5V 至 ±18V
- 单电源电压范围：4.5V 至 36V
- 低导通电阻：2Ω
- -40°C 至 +125°C 工作温度
- 逻辑电平：1.8V 至 VDD
- 失效防护逻辑
- 轨至轨运行
- 双向运行
- 先断后合开关
- ESD 保护 HBM：2000V

2 应用

- 采样和保持电路
- 反馈增益开关
- 信号隔离
- 现场发送器
- 可编程逻辑控制器 (PLC)
- 工厂自动化和控制
- 超声波扫描仪
- 患者监护和诊断
- 心电图 (ECG)
- 数据采集系统 (DAQ)
- 半导体测试设备
- LCD 测试
- 仪表：实验室、分析、便携仪表
- 超声波智能仪表：水表和燃气表
- 光纤网络
- 光学测试设备

3 说明

TMUX6211、TMUX6212 和 TMUX6213 是互补金属氧化物半导体 (CMOS) 开关，具有四个独立可选的 1:1 单极单掷 (SPST) 开关通道。这些器件在双电源 (±4.5V 至 ±18V)、单电源 (4.5V 至 36V) 或非对称电源 (例如 $V_{DD} = 12V$, $V_{SS} = -5V$) 供电时均能正常运行。TMUX621x 可在源极 (Sx) 和漏极 (D) 引脚上支持从 V_{SS} 到 V_{DD} 范围的双向模拟和数字信号。

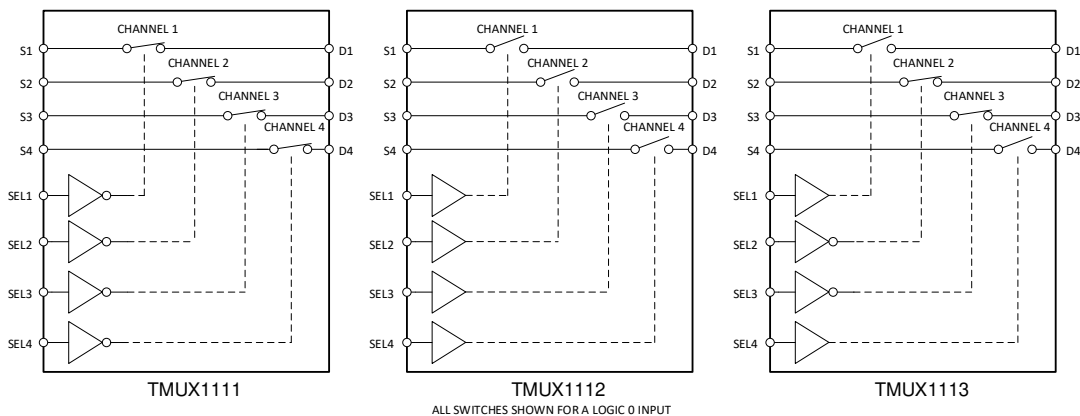
TMUX6211 的开关可通过逻辑 0 在恰当的逻辑控制输入下打开，而要打开 TMUX6212 中的开关，则需逻辑 1。TMUX6213 的四个通道通过两个支持逻辑 0 的开关分开，而另外两个开关则支持逻辑 1。TMUX6213 具有先断后合开关，因此该器件可用于交叉点开关应用。

TMUX621x 是精密开关和多路复用器系列器件。这些器件具有非常低的导通和关断泄漏电流以及较低的电荷注入，因此可用于高精度测量应用。

器件信息 (1)

器件型号	封装	封装尺寸 (标称值)
TMUX6211	TSSOP (16) (PW)	5.00mm × 4.40mm
TMUX6212	WQFN (16) (RUM)	4.00mm × 4.00mm
TMUX6213		

(1) 如需了解所有可用封装，请参阅数据表末尾的封装选项附录。



TMUX621x 方框图



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4 Revision History

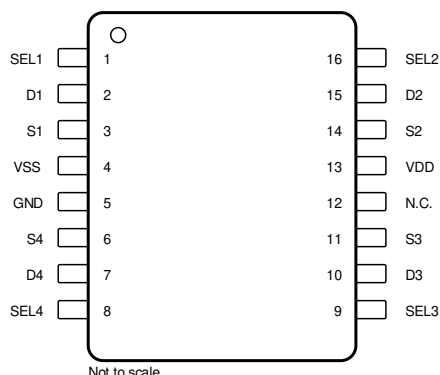
注：以前版本的页码可能与当前版本的页码不同

DATE	REVISION	NOTES
October 2020	*	Initial Release

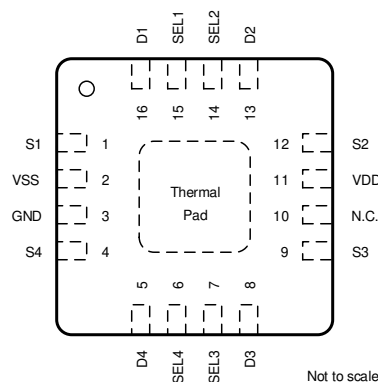
5 Device Comparison Table

PRODUCT	DESCRIPTION
TMUX6211	Low-Leakage-Current, Precision, 4-Channel, 1:1 (SPST) Switches (Normally Closed)
TMUX6212	Low-Leakage-Current, Precision, 4-Channel, 1:1 (SPST) Switches (Normally Open)
TMUX6213	Low-Leakage-Current, Precision, 4-Channel, 1:1 (SPST) Switches (Dual Open + Dual Closed)

6 Pin Configuration and Functions



**图 6-1. PW Package
16-Pin TSSOP
Top View**



**图 6-2. RUM Package
16-Pin WQFN
Top View**

表 6-1. Pin Functions

PIN			TYPE ⁽¹⁾	DESCRIPTION ⁽²⁾
NAME	TSSOP	WQFN		
SEL1	1	15	I	Logic control input 1, has internal pull-down resistor. Controls channel 1 state as shown in 节 8.5.
D1	2	16	I/O	Drain pin 1. Can be an input or output.
S1	3	1	I/O	Source pin 1. Can be an input or output.
VSS	4	2	P	Negative power supply. This pin is the most negative power-supply potential. In single-supply applications, this pin can be connected to ground. For reliable operation, connect a decoupling capacitor ranging from 0.1 μ F to 10 μ F between V_{SS} and GND.
GND	5	3	P	Ground (0 V) reference
S4	6	4	I/O	Source pin 4. Can be an input or output.
D4	7	5	I/O	Drain pin 4. Can be an input or output.
SEL4	8	6	I	Logic control input 4, has internal pull-down resistor. Controls channel 4 state as shown in 节 8.5.
SEL3	9	7	I	Logic control input 3, has internal pull-down resistor. Controls channel 3 state as shown in 节 8.5.
D3	10	8	I/O	Drain pin 3. Can be an input or output.
S3	11	9	I/O	Source pin 3. Can be an input or output.
N.C.	12	10	-	No internal connection.
VDD	13	11	P	Positive power supply. This pin is the most positive power-supply potential. For reliable operation, connect a decoupling capacitor ranging from 0.1 μ F to 10 μ F between V_{DD} and GND.
S2	14	12	I/O	Source pin 2. Can be an input or output.
D2	15	13	I/O	Drain pin 2. Can be an input or output.
SEL2	16	14	I	Logic control input 2, has internal pull-down resistor. Controls channel 2 state as shown in 节 8.5.

(1) I = input, O = output, I/O = input and output, P = power.

(2) Refer to 节 8.4 for what to do with unused pins.

7 Specifications

7.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)^{(1) (2) (3)}

		MIN	MAX	UNIT
$V_{DD}-V_{SS}$	Supply voltage		38	V
V_{DD}		-0.5	38	V
V_{SS}		-38	0.5	V
V_{SEL} or V_{EN}	Logic control input pin voltage (SELx) ⁽⁴⁾	-0.5	38	V
I_{SEL} or I_{EN}	Logic control input pin current (SELx) ⁽⁴⁾	-30	30	mA
V_S or V_D	Source or drain voltage (Sx, Dx) ⁽⁴⁾	$V_{SS}-0.5$	$V_{DD}+0.5$	V
I_{IK}	Diode clamp current ⁽⁴⁾	-30	30	mA
I_S or I_D (CONT)	Source or drain continuous current (Sx, Dx)	$I_{DC} + 10\%$ ⁽⁵⁾		mA
T_A	Ambient temperature	-55	135	°C
T_{stg}	Storage temperature	-65	150	°C
T_J	Junction temperature		140	°C

- (1) Stresses beyond those listed under *Absolute Maximum Rating* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Condition*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum.
- (3) All voltages are with respect to ground, unless otherwise specified.
- (4) Pins are diode-clamped to the power-supply rails. Over voltage signals must be voltage and current limited to maximum ratings.
- (5) Refer to *Source or Drain Continuous Current* table for I_{DC} specifications.

7.2 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001, all pins ⁽¹⁾	±2000	V
		Charged device model (CDM), per JEDEC specification JESD22-C101, all pins ⁽²⁾	±500	

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

7.3 Thermal Information

THERMAL METRIC ⁽¹⁾		TMUX721x		UNIT
		PW (TSSOP)	RUM (WQFN)	
		16 PINS	16 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	94.5	TBD	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	25.5	TBD	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	41.1	TBD	°C/W
Ψ_{JT}	Junction-to-top characterization parameter	1.1	TBD	°C/W
Ψ_{JB}	Junction-to-board characterization parameter	40.4	TBD	°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	N/A	TBD	°C/W

- (1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics](#) application report.

7.4 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
$V_{DD} - V_{SS}$ ⁽¹⁾	Power supply voltage differential	4.5		36	V
V_{DD}	Positive power supply voltage	4.5		36	V
V_S or V_D	Signal path input/output voltage (source or drain pin) (Sx, D)	V_{SS}		V_{DD}	V
V_{SEL} or V_{EN}	Address or enable pin voltage	0		36	V
I_S or I_D (CONT)	Source or drain continuous current (Sx, D)		I_{DC} ⁽²⁾		
T_A	Ambient temperature	–40		125	°C

(1) V_{DD} and V_{SS} can be any value as long as $4.5\text{ V} \leq (V_{DD} - V_{SS}) \leq 36\text{ V}$, and the minimum V_{DD} is met.

(2) Refer to *Source or Drain Continuous Current* table for I_{DC} specifications.

7.5 Source or Drain Continuous Current

at supply voltage of $V_{DD} \pm 10\%$, $V_{SS} \pm 10\%$ (unless otherwise noted)

CONTINUOUS CURRENT PER CHANNEL (I_{DC})		$T_A = 25^\circ\text{C}$	$T_A = 85^\circ\text{C}$	$T_A = 125^\circ\text{C}$	UNIT
PACKAGE	TEST CONDITIONS				
PW (TSSOP)	±15 V Dual Supply	370	240	145	mA
	+12 V Single Supply	270	190	120	mA
	±5 V Dual Supply	260	180	118	mA
	+5 V Single Supply	200	140	100	mA

7.6 ±15 V Dual Supply: Electrical Characteristics

$V_{DD} = +15\text{ V} \pm 10\%$, $V_{SS} = -15\text{ V} \pm 10\%$, $GND = 0\text{ V}$ (unless otherwise noted)

Typical at $V_{DD} = +15\text{ V}$, $V_{SS} = -15\text{ V}$, $T_A = 25^\circ\text{C}$ (unless otherwise noted)

PARAMETER		TEST CONDITIONS	T _A	MIN	TYP	MAX	UNIT
ANALOG SWITCH							
R _{ON}	On-resistance	V _S = −10 V to +10 V I _D = −10 mA	25°C		2	3	Ω
			−40°C to +85°C			3.9	Ω
			−40°C to +125°C			4.6	Ω
ΔR _{ON}	On-resistance mismatch between channels	V _S = −10 V to +10 V I _D = −10 mA	25°C		0.05	0.2	Ω
			−40°C to +85°C			0.25	Ω
			−40°C to +125°C			0.3	Ω
R _{ON FLAT}	On-resistance flatness	V _S = −10 V to +10 V I _S = −10 mA	25°C		0.45	0.65	Ω
			−40°C to +85°C			0.8	Ω
			−40°C to +125°C			0.95	Ω
R _{ON DRIFT}	On-resistance drift	V _S = 0 V, I _S = −10 mA	−40°C to +125°C		0.01		Ω/°C
I _{S(OFF)}	Source off leakage current ⁽¹⁾	V _{DD} = 16.5 V, V _{SS} = −16.5 V Switch state is off V _S = +10 V / −10 V V _D = −10 V / + 10 V	25°C		0.05		nA
			−40°C to +85°C		0.5		nA
			−40°C to +125°C	−35		35	nA
I _{D(OFF)}	Drain off leakage current ⁽¹⁾	V _{DD} = 16.5 V, V _{SS} = −16.5 V Switch state is off V _S = +10 V / −10 V V _D = −10 V / + 10 V	25°C		0.05		nA
			−40°C to +85°C		1		nA
			−40°C to +125°C	−60		60	nA
I _{S(ON)} I _{D(ON)}	Channel on leakage current ⁽²⁾	V _{DD} = 16.5 V, V _{SS} = −16.5 V Switch state is on V _S = V _D = ±10 V	25°C		0.05		nA
			−40°C to +85°C		1		nA
			−40°C to +125°C	−60		60	nA
LOGIC INPUTS (SEL / EN pins)							
V _{IH}	Logic voltage high		−40°C to +125°C	1.3		36	V
V _{IL}	Logic voltage low		−40°C to +125°C	0		0.8	V
I _{IH}	Input leakage current		−40°C to +125°C		0.4	1.2	μA
I _{IL}	Input leakage current		−40°C to +125°C	−0.1	−0.005		μA
C _{IN}	Logic input capacitance		−40°C to +125°C		3		pF
POWER SUPPLY							
I _{DD}	V _{DD} supply current	V _{DD} = 16.5 V, V _{SS} = −16.5 V Logic inputs = 0 V, 5 V, or V _{DD}	25°C		35	65	μA
			−40°C to +85°C			72	μA
			−40°C to +125°C			92	μA
I _{SS}	V _{SS} supply current	V _{DD} = 16.5 V, V _{SS} = −16.5 V Logic inputs = 0 V, 5 V, or V _{DD}	25°C		15	25	μA
			−40°C to +85°C			30	μA
			−40°C to +125°C			45	μA

(1) When V_S is positive, V_D is negative, or when V_S is negative, V_D is positive.

(2) When V_S is at a voltage potential, V_D is floating, or when V_D is at a voltage potential, V_S is floating.

7.7 ±15 V Dual Supply: Switching Characteristics

$V_{DD} = +15\text{ V} \pm 10\%$, $V_{SS} = -15\text{ V} \pm 10\%$, $GND = 0\text{ V}$ (unless otherwise noted)

Typical at $V_{DD} = +15\text{ V}$, $V_{SS} = -15\text{ V}$, $T_A = 25^\circ\text{C}$ (unless otherwise noted)

PARAMETER		TEST CONDITIONS	T_A	MIN	TYP	MAX	UNIT
t_{TRAN}	Transition time from control input	$V_S = 10\text{ V}$ $R_L = 300\ \Omega$, $C_L = 35\text{ pF}$	25°C		100	150	ns
			-40°C to $+85^\circ\text{C}$			170	ns
			-40°C to $+125^\circ\text{C}$			190	ns
t_{ON}	Turn-on time from control input	$V_S = 10\text{ V}$ $R_L = 300\ \Omega$, $C_L = 35\text{ pF}$	25°C		130	170	ns
			-40°C to $+85^\circ\text{C}$			190	ns
			-40°C to $+125^\circ\text{C}$			210	ns
t_{OFF}	Turn-off time from control input	$V_S = 10\text{ V}$ $R_L = 300\ \Omega$, $C_L = 35\text{ pF}$	25°C		110	185	ns
			-40°C to $+85^\circ\text{C}$			200	ns
			-40°C to $+125^\circ\text{C}$			210	ns
t_{PD}	Propagation delay	$R_L = 50\ \Omega$, $C_L = 5\text{ pF}$	25°C		100		ps
Q_{INJ}	Charge injection	$V_S = 0\text{ V}$, $C_L = 1\text{ nF}$	25°C		15		pC
O_{ISO}	Off-isolation	$R_L = 50\ \Omega$, $C_L = 5\text{ pF}$ $V_S = 0\text{ V}$, $f = 100\text{ kHz}$	25°C		-70		dB
X_{TALK}	Crosstalk	$R_L = 50\ \Omega$, $C_L = 5\text{ pF}$ $V_S = 0\text{ V}$, $f = 100\text{ kHz}$	25°C		-100		dB
BW	-3dB Bandwidth	$R_L = 50\ \Omega$, $C_L = 5\text{ pF}$ $V_S = 0\text{ V}$	25°C		45		MHz
$C_{\text{S(OFF)}}$	Source off capacitance	$V_S = 0\text{ V}$, $f = 1\text{ MHz}$	25°C		30		pF
$C_{\text{D(OFF)}}$	Drain off capacitance	$V_S = 0\text{ V}$, $f = 1\text{ MHz}$	25°C		45		pF
$C_{\text{S(ON)}}$, $C_{\text{D(ON)}}$	On capacitance	$V_S = 0\text{ V}$, $f = 1\text{ MHz}$	25°C		145		pF

7.8 12 V Single Supply: Electrical Characteristics

$V_{DD} = +12\text{ V} \pm 10\%$, $V_{SS} = 0\text{ V}$, $GND = 0\text{ V}$ (unless otherwise noted)

Typical at $V_{DD} = +12\text{ V}$, $V_{SS} = 0\text{ V}$, $T_A = 25^\circ\text{C}$ (unless otherwise noted)

PARAMETER		TEST CONDITIONS	T _A	MIN	TYP	MAX	UNIT
ANALOG SWITCH							
R _{ON}	On-resistance	V _S = 0 V to 10 V I _D = −10 mA	25°C		4	6.2	Ω
			−40°C to +85°C			7.5	Ω
			−40°C to +125°C			8.5	Ω
ΔR _{ON}	On-resistance mismatch between channels	V _S = 0 V to 10 V I _D = −10 mA	25°C		0.08	0.32	Ω
			−40°C to +85°C			0.4	Ω
			−40°C to +125°C			0.45	Ω
R _{ON FLAT}	On-resistance flatness	V _S = 0 V to 10 V I _S = −10 mA	25°C		1.2	2.2	Ω
			−40°C to +85°C			2.6	Ω
			−40°C to +125°C			2.8	Ω
R _{ON DRIFT}	On-resistance drift	V _S = 6 V, I _S = −10 mA	−40°C to +125°C		0.015		Ω/°C
I _{S(OFF)}	Source off leakage current ⁽¹⁾	V _{DD} = 13.2 V, V _{SS} = 0 V Switch state is off V _S = 10 V / 1 V V _D = 1 V / 10 V	25°C		0.05		nA
			−40°C to +85°C		0.5		nA
			−40°C to +125°C	−35		35	nA
I _{D(OFF)}	Drain off leakage current ⁽¹⁾	V _{DD} = 13.2 V, V _{SS} = 0 V Switch state is off V _S = 10 V / 1 V V _D = 1 V / 10 V	25°C		0.05		nA
			−40°C to +85°C		1		nA
			−40°C to +125°C	−60		60	nA
I _{S(ON)} I _{D(ON)}	Channel on leakage current ⁽²⁾	V _{DD} = 13.2 V, V _{SS} = 0 V Switch state is on V _S = V _D = 10 V or 1 V	25°C		0.05		nA
			−40°C to +85°C		1		nA
			−40°C to +125°C	−60		60	nA
LOGIC INPUTS (SEL / EN pins)							
V _{IH}	Logic voltage high		−40°C to +125°C	1.3		36	V
V _{IL}	Logic voltage low		−40°C to +125°C	0		0.8	V
I _{IH}	Input leakage current		−40°C to +125°C		0.4	1.2	μA
I _{IL}	Input leakage current		−40°C to +125°C	−0.1	−0.005		μA
C _{IN}	Logic input capacitance		−40°C to +125°C		3		pF
POWER SUPPLY							
I _{DD}	V _{DD} supply current	V _{DD} = 13.2 V, V _{SS} = 0 V Logic inputs = 0 V, 5 V, or V _{DD}	25°C		35	55	μA
			−40°C to +85°C			68	μA
			−40°C to +125°C			80	μA

(1) When V_S is positive, V_D is negative, or when V_S is negative, V_D is positive.

(2) When V_S is at a voltage potential, V_D is floating, or when V_D is at a voltage potential, V_S is floating.

7.9 12 V Single Supply: Switching Characteristics

$V_{DD} = +12\text{ V} \pm 10\%$, $V_{SS} = 0\text{ V}$, $GND = 0\text{ V}$ (unless otherwise noted)

Typical at $V_{DD} = +12\text{ V}$, $V_{SS} = 0\text{ V}$, $T_A = 25^\circ\text{C}$ (unless otherwise noted)

PARAMETER		TEST CONDITIONS	T_A	MIN	TYP	MAX	UNIT
t_{TRAN}	Transition time from control input	$V_S = 8\text{ V}$ $R_L = 300\ \Omega$, $C_L = 35\text{ pF}$	25°C		170	250	ns
			-40°C to $+85^\circ\text{C}$			290	ns
			-40°C to $+125^\circ\text{C}$			330	ns
t_{ON}	Turn-on time from control input	$V_S = 8\text{ V}$ $R_L = 300\ \Omega$, $C_L = 35\text{ pF}$	25°C		170	200	ns
			-40°C to $+85^\circ\text{C}$			250	ns
			-40°C to $+125^\circ\text{C}$			275	ns
t_{OFF}	Turn-off time from control input	$V_S = 8\text{ V}$ $R_L = 300\ \Omega$, $C_L = 35\text{ pF}$	25°C		200	220	ns
			-40°C to $+85^\circ\text{C}$			250	ns
			-40°C to $+125^\circ\text{C}$			270	ns
t_{PD}	Propagation delay	$R_L = 50\ \Omega$, $C_L = 5\text{ pF}$	25°C		100		ps
Q_{INJ}	Charge injection	$V_S = 6\text{ V}$, $C_L = 1\text{ nF}$	25°C		13		pC
O_{ISO}	Off-isolation	$R_L = 50\ \Omega$, $C_L = 5\text{ pF}$ $V_S = 6\text{ V}$, $f = 100\text{ kHz}$	25°C		-70		dB
X_{TALK}	Crosstalk	$R_L = 50\ \Omega$, $C_L = 5\text{ pF}$ $V_S = 6\text{ V}$, $f = 100\text{ kHz}$	25°C		-95		dB
BW	-3dB Bandwidth	$R_L = 50\ \Omega$, $C_L = 5\text{ pF}$ $V_S = 6\text{ V}$	25°C		80		MHz
$C_{\text{S(OFF)}}$	Source off capacitance	$V_S = 6\text{ V}$, $f = 1\text{ MHz}$	25°C		35		pF
$C_{\text{D(OFF)}}$	Drain off capacitance	$V_S = 6\text{ V}$, $f = 1\text{ MHz}$	25°C		50		pF
$C_{\text{S(ON)}}$, $C_{\text{D(ON)}}$	On capacitance	$V_S = 6\text{ V}$, $f = 1\text{ MHz}$	25°C		142		pF

7.10 ± 5 V Dual Supply: Electrical Characteristics

$V_{DD} = +5\text{ V} \pm 10\%$, $V_{SS} = -5\text{ V} \pm 10\%$, GND = 0 V (unless otherwise noted)

Typical at $V_{DD} = +5\text{ V}$, $V_{SS} = -5\text{ V}$, $T_A = 25^\circ\text{C}$ (unless otherwise noted)

PARAMETER		TEST CONDITIONS	T _A	MIN	TYP	MAX	UNIT
ANALOG SWITCH							
R _{ON}	On-resistance	V _{DD} = +4.5 V, V _{SS} = −4.5 V V _S = −4.5 V to +4.5 V I _D = −10 mA	25°C		4	7.3	Ω
			−40°C to +85°C			8.8	Ω
			−40°C to +125°C			9.8	Ω
ΔR _{ON}	On-resistance mismatch between channels	V _S = −4.5 V to +4.5 V I _D = −10 mA	25°C		0.1	0.3	Ω
			−40°C to +85°C			0.35	Ω
			−40°C to +125°C			0.4	Ω
R _{ON FLAT}	On-resistance flatness	V _S = −4.5 V to +4.5 V I _D = −10 mA	25°C		1.8	2.3	Ω
			−40°C to +85°C			2.8	Ω
			−40°C to +125°C			3.5	Ω
R _{ON DRIFT}	On-resistance drift	V _S = 0 V, I _S = −10 mA	−40°C to +125°C		0.02		Ω/°C
I _{S(OFF)}	Source off leakage current ⁽¹⁾	V _{DD} = +5.5 V, V _{SS} = −5.5 V Switch state is off V _S = +4.5 V / −4.5 V V _D = −4.5 V / + 4.5 V	25°C		0.05		nA
			−40°C to +85°C		0.5		nA
			−40°C to +125°C	−35		35	nA
I _{D(OFF)}	Drain off leakage current ⁽¹⁾	V _{DD} = +5.5 V, V _{SS} = −5.5 V Switch state is off V _S = +4.5 V / −4.5 V V _D = −4.5 V / + 4.5 V	25°C		0.05		nA
			−40°C to +85°C		1		nA
			−40°C to +125°C	−60		60	nA
I _{S(ON)} I _{D(ON)}	Channel on leakage current ⁽²⁾	V _{DD} = +5.5 V, V _{SS} = −5.5 V Switch state is on V _S = V _D = ±4.5 V	25°C		0.05		nA
			−40°C to +85°C		1		nA
			−40°C to +125°C	−60		60	nA
LOGIC INPUTS (SEL / EN pins)							
V _{IH}	Logic voltage high		−40°C to +125°C		1.3		36 V
V _{IL}	Logic voltage low		−40°C to +125°C		0		0.8 V
I _{IH}	Input leakage current		−40°C to +125°C		0.4		1.2 μA
I _{IL}	Input leakage current		−40°C to +125°C	−0.1	−0.005		μA
C _{IN}	Logic input capacitance		−40°C to +125°C		3		pF
POWER SUPPLY							
I _{DD}	V _{DD} supply current	V _{DD} = +5.5 V, V _{SS} = −5.5 V Logic inputs = 0 V, 5 V, or V _{DD}	25°C		33	50	μA
			−40°C to +85°C			55	μA
			−40°C to +125°C			65	μA
I _{SS}	V _{SS} supply current	V _{DD} = +5.5 V, V _{SS} = −5.5 V Logic inputs = 0 V, 5 V, or V _{DD}	25°C		4	10	μA
			−40°C to +85°C			15	μA
			−40°C to +125°C			25	μA

(1) When V_S is positive, V_D is negative, or when V_S is negative, V_D is positive.

(2) When V_S is at a voltage potential, V_D is floating, or when V_D is at a voltage potential, V_S is floating.

7.11 ± 5 V Dual Supply: Switching Characteristics

$V_{DD} = +5\text{ V} \pm 10\%$, $V_{SS} = -5\text{ V} \pm 10\%$, $GND = 0\text{ V}$ (unless otherwise noted)

Typical at $V_{DD} = +5\text{ V}$, $V_{SS} = -5\text{ V}$, $T_A = 25^\circ\text{C}$ (unless otherwise noted)

PARAMETER		TEST CONDITIONS	T_A	MIN	TYP	MAX	UNIT
t_{TRAN}	Transition time from control input	$V_S = 3\text{ V}$ $R_L = 300\ \Omega$, $C_L = 35\text{ pF}$	25°C		270	400	ns
			-40°C to $+85^\circ\text{C}$			465	ns
			-40°C to $+125^\circ\text{C}$			510	ns
t_{ON}	Turn-on time from control input	$V_S = 3\text{ V}$ $R_L = 300\ \Omega$, $C_L = 35\text{ pF}$	25°C		220	250	ns
			-40°C to $+85^\circ\text{C}$			285	ns
			-40°C to $+125^\circ\text{C}$			315	ns
t_{OFF}	Turn-off time from control input	$V_S = 3\text{ V}$ $R_L = 300\ \Omega$, $C_L = 35\text{ pF}$	25°C		170	270	ns
			-40°C to $+85^\circ\text{C}$			300	ns
			-40°C to $+125^\circ\text{C}$			315	ns
t_{PD}	Propagation delay	$R_L = 50\ \Omega$, $C_L = 5\text{ pF}$	25°C		100		ps
Q_{INJ}	Charge injection	$V_S = 0\text{ V}$, $C_L = 1\text{ nF}$	25°C		15		pC
O_{ISO}	Off-isolation	$R_L = 50\ \Omega$, $C_L = 5\text{ pF}$ $V_S = 0\text{ V}$, $f = 100\text{ kHz}$	25°C		-70		dB
X_{TALK}	Crosstalk	$R_L = 50\ \Omega$, $C_L = 5\text{ pF}$ $V_S = 0\text{ V}$, $f = 100\text{ kHz}$	25°C		-95		dB
BW	-3dB Bandwidth	$R_L = 50\ \Omega$, $C_L = 5\text{ pF}$ $V_S = 0\text{ V}$	25°C		90		MHz
$C_{\text{S(OFF)}}$	Source off capacitance	$V_S = 0\text{ V}$, $f = 1\text{ MHz}$	25°C		35		pF
$C_{\text{D(OFF)}}$	Drain off capacitance	$V_S = 0\text{ V}$, $f = 1\text{ MHz}$	25°C		52		pF
$C_{\text{S(ON)}}$, $C_{\text{D(ON)}}$	On capacitance	$V_S = 0\text{ V}$, $f = 1\text{ MHz}$	25°C		142		pF

8 Detailed Description

8.1 Overview

The TMUX6211, TMUX6212, and TMUX6213 are 1:1 (SPST), 4-Channel switches. The devices have four independently selectable single-pole, single-throw switches that are turned-on or turned-off based on the state of the corresponding select pin.

8.2 Functional Block Diagram

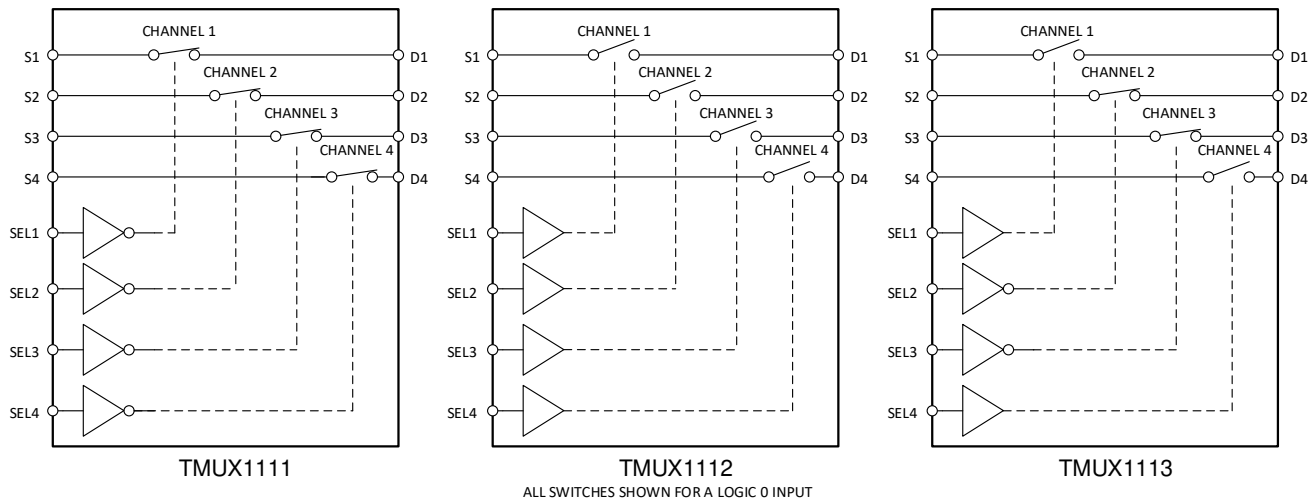


图 8-1. TMUX621x Functional Block Diagram

8.3 Feature Description

8.3.1 Bidirectional Operation

The TMUX621x conducts equally well from source (Sx) to drain (Dx) or from drain (Dx) to source (Sx). Each channel has very similar characteristics in both directions and supports both analog and digital signals.

8.3.2 Rail-to-Rail Operation

The valid signal path input and output voltage for TMUX621x ranges from V_{SS} to V_{DD} .

8.3.3 1.8 V Logic Compatible Inputs

The TMUX621x devices have 1.8-V logic compatible control for all logic control inputs. 1.8-V logic level inputs allows the TMUX621x to interface with processors that have lower logic I/O rails and eliminates the need for an external translator, which saves both space and BOM cost. For more information on 1.8 V logic implementations refer to [Simplifying Design with 1.8 V logic Muxes and Switches](#).

8.3.4 Fail-Safe Logic

The TMUX621x supports Fail-Safe Logic on the control input pins (SEL1, SEL2, SEL3, and SEL4) allowing for operation up to 36 V, regardless of the state of the supply pin. This feature allows voltages on the control pins to be applied before the supply pin, protecting the device from potential damage. Fail-Safe Logic minimizes system complexity by removing the need for power supply sequencing on the logic control pins. For example, the Fail-Safe Logic feature allows the select pins of the TMUX621x to be ramped to 36 V while V_{DD} and V_{SS} = 0 V. The logic control inputs are protected against positive faults of up to 36 V in powered-off condition, but do not offer protection against negative overvoltage conditions.

8.4 Device Functional Modes

The TMUX621x devices have four independently selectable single-pole, single-throw switches that are turned-on or turned-off based on the state of the corresponding select pin. The control pins can be as high as 36 V.

The TMUX621x devices can be operated without any external components except for the supply decoupling capacitors. Unused logic control pins should be tied to GND or V_{DD} in order to ensure the device does not consume additional current as highlighted in [Implications of Slow or Floating CMOS Inputs](#). Unused signal path inputs (Sx or Dx) should be connection to GND.

8.5 Truth Tables

表 8-1, 表 8-2, and 表 8-3 show the truth tables for the TMUX6211, TMUX6212, and TMUX6213, respectively.

表 8-1. TMUX6211 Truth Table

SEL x ⁽¹⁾	CHANNEL x
0	Channel x ON
1	Channel x OFF

表 8-2. TMUX6212 Truth Table

SEL x ⁽¹⁾	CHANNEL x
0	Channel x OFF
1	Channel x ON

表 8-3. TMUX6213 Truth Table

SEL x ⁽¹⁾	CHANNEL 1 / CHANNEL 4	CHANNEL 2 / CHANNEL 3
0	OFF	ON
1	ON	OFF

(1) x denotes 1, 2, 3, or 4 for the corresponding channel.

9 Application and Implementation

Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

9.1 Application Information

The TMUX621x is part of the precision switches and multiplexers family of devices. These devices operate with dual supplies (± 4.5 V to ± 18 V), a single supply (4.5 V to 36 V), or asymmetric supplies (such as $V_{DD} = 12$ V, $V_{SS} = -5$ V), and offer true rail-to-rail input and output. The TMUX621x offers low R_{ON} , low on and off leakage currents and ultra-low charge injection performance. These features makes the TMUX621x a family of precision, robust, high-performance analog multiplexer for high-voltage, industrial applications.

9.2 Typical Application

One example to take advantage of TMUX621x precision performance is the implementation of parametric measurement unit (PMU) in the semiconductor automatic test equipment (ATE) application.

In Automated Test Equipment (ATE) systems, the Parametric Measurement Unit (PMU) is tasked to measure device (DUT) parametric information in terms of voltage and current. When measuring voltage, current is applied at the DUT pin, and current range adjustment can be done through changing the value of the internal sense resistor. There is sometimes a need, depending on the DUT, to use even higher testing current than natively supported by the system. A 4 channel SPST switch, together with external higher current amplifier and resistor, can be used to achieve the flexibility. The PMU operating voltage is typically in mid voltage (up to 20 V). An appropriate switch like the TMUX621x with low leakage current (0.05 nA typical) works well in these applications to ensure measurement accuracy and low R_{ON} and flat $R_{ON_FLATNESS}$ allows the current range to be controlled more precisely. 图 9-1 shows simplified diagram of such implementations in memory and semiconductor test equipment.

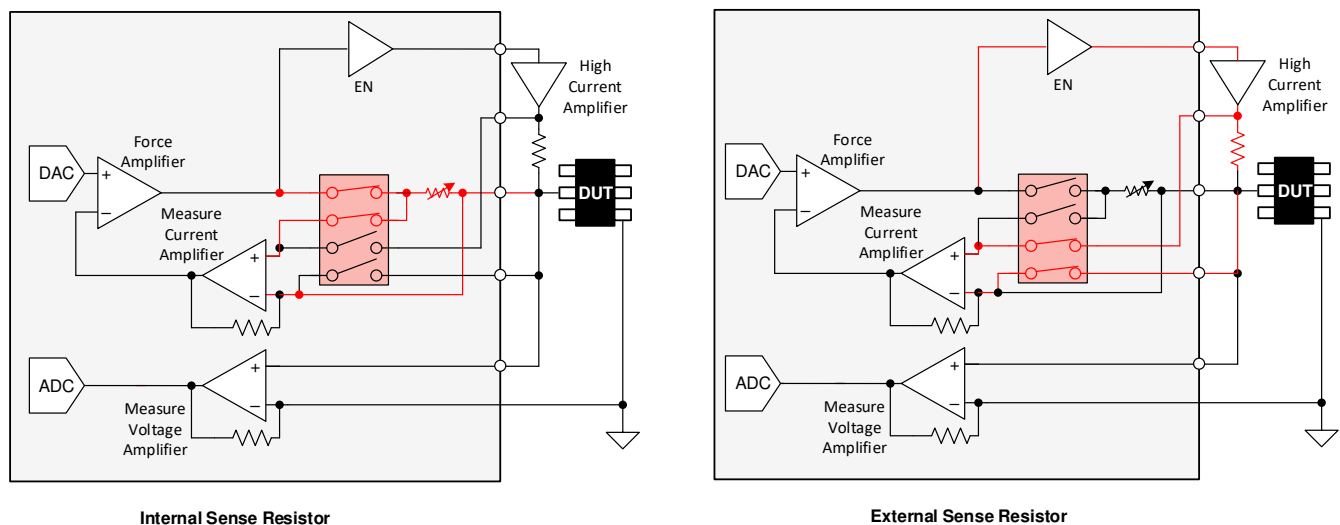


图 9-1. High Current Range Selection Using External Resistor

9.3 Design Requirements

For this design example, use the parameters listed in [表 9-1](#).

表 9-1. Design Parameters

PARAMETERS	VALUES
Supply (V_{DD})	20 V
Supply (V_{SS})	- 10 V
Input / Output signal range	-10 V to 20 V (Rail-to-Rail)
Control logic thresholds	1.8 V compatible

9.4 Detailed Design Procedure

The application shown in [High Current Range Selection Using External Resistor](#) figure demonstrates how the TMUX621x can be used in semiconductor test equipment for high-precision, high-voltage, multi-channel measurement applications. The TMUX621x can support 1.8-V logic signals on the control input, allowing the device to interface with low logic controls of an FPGA or MCU. The TMUX621x can be operated without any external components except for the supply decoupling capacitors. The select pins have an internal pull-down resistor to prevent floating input logic. All inputs to the switch must fall within the recommend operating conditions of the TMUX621x including signal range and continuous current. For this design with a positive supply of 20 V on V_{DD} , and negative supply of -10 V on V_{SS} , the signal range can be 20 V to -10 V. The max continuous current (I_{DC}) can be up to 370 mA as shown in the *Recommended Operating Conditions* table for wide-range current measurement.

10 Power Supply Recommendations

The TMUX621x operates across a wide supply range of $\pm 4.5\text{ V}$ to $\pm 18\text{ V}$ (4.5 V to 36 V in single-supply mode). The device also perform well with asymmetrical supplies such as $V_{DD} = 12\text{ V}$ and $V_{SS} = -5\text{ V}$.

Power-supply bypassing improves noise margin and prevents switching noise propagation from the supply rails to other components. Good power-supply decoupling is important to achieve optimum performance. For improved supply noise immunity, use a supply decoupling capacitor ranging from 0.1 μF to 10 μF at both the V_{DD} and V_{SS} pins to ground. Place the bypass capacitors as close to the power supply pins of the device as possible using low-impedance connections. TI recommends using multi-layer ceramic chip capacitors (MLCCs) that offer low equivalent series resistance (ESR) and inductance (ESL) characteristics for power-supply decoupling purposes. For very sensitive systems, or for systems in harsh noise environments, avoiding the use of vias for connecting the capacitors to the device pins may offer superior noise immunity. The use of multiple vias in parallel lowers the overall inductance and is beneficial for connections to ground planes. Always ensure the ground (GND) connection is established before supplies are ramped.

11 Layout

11.1 Layout Guidelines

When a PCB trace turns a corner at a 90° angle, a reflection can occur. A reflection occurs primarily because of the change of width of the trace. At the apex of the turn, the trace width increases to 1.414 times the width. This increase upsets the transmission-line characteristics, especially the distributed capacitance and self-inductance of the trace which results in the reflection. Not all PCB traces can be straight and therefore some traces must turn corners. 图 11-1 shows progressively better techniques of rounding corners. Only the last example (BEST) maintains constant trace width and minimizes reflections.

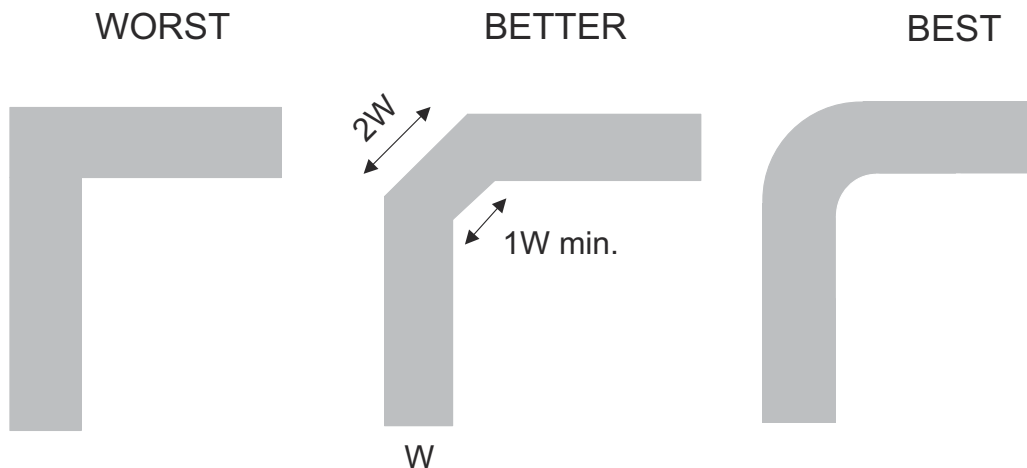


图 11-1. Trace Example

Route high-speed signals using a minimum of vias and corners which reduces signal reflections and impedance changes. When a via must be used, increase the clearance size around it to minimize its capacitance. Each via introduces discontinuities in the signal's transmission line and increases the chance of picking up interference from the other layers of the board. Be careful when designing test points, through-hole pins are not recommended at high frequencies.

图 11-2 illustrates an example of a PCB layout with the TMUX621x.

Some key considerations are:

- Decouple the supply pins with a 0.1-μF and 1 μF capacitor, placed lowest value capacitor as close to the pin as possible. Make sure that the capacitor voltage rating is sufficient for the supply voltage.
- Keep the input lines as short as possible.
- Use a solid ground plane to help reduce electromagnetic interference (EMI) noise pickup.
- Do not run sensitive analog traces in parallel with digital traces. Avoid crossing digital and analog traces if possible, and only make perpendicular crossings when necessary.
- Using multiple vias in parallel will lower the overall inductance and is beneficial for connection to ground planes.

11.2 Layout Example

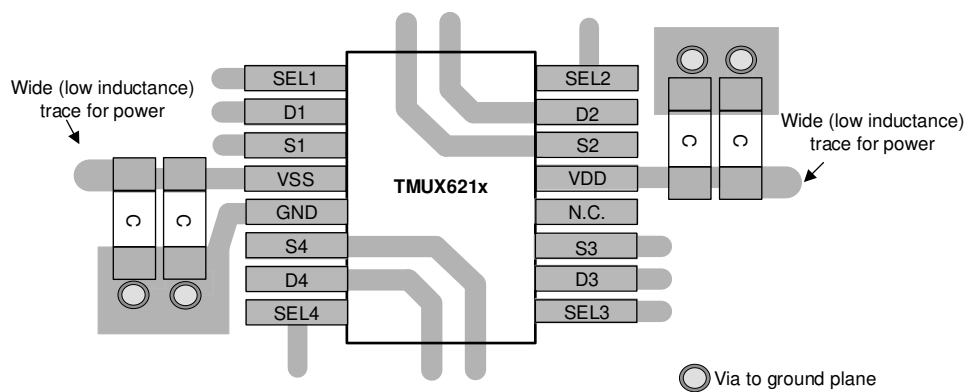


图 11-2. TMUX621x Layout Example

12 Device and Documentation Support

12.1 Documentation Support

12.1.1 Related Documentation

Texas Instruments, [Sample & Hold Glitch Reduction for Precision Outputs Reference Design](#).

Texas Instruments, [True Differential, 4 x 2 MUX, Analog Front End, Simultaneous-Sampling ADC Circuit](#).

Texas Instruments, [Improve Stability Issues with Low CON Multiplexers](#).

Texas Instruments, [Simplifying Design with 1.8 V logic Muxes and Switches](#).

Texas Instruments, [Eliminate Power Sequencing with Powered-off Protection Signal Switches](#).

Texas Instruments, [System-Level Protection for High-Voltage Analog Multiplexers](#).

Texas Instruments, [QFN/SON PCB Attachment](#).

Texas Instruments, [Quad Flatpack No-Lead Logic Packages](#).

12.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on [ti.com](#). Click on [Subscribe to updates](#) to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

12.3 Support Resources

[TI E2E™ support forums](#) are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

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12.4 Trademarks

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12.5 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

12.6 Glossary

[TI Glossary](#) This glossary lists and explains terms, acronyms, and definitions.

13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
TMUX6211PWR	PREVIEW	TSSOP	PW	16	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	X211	
TMUX6211RUMR	PREVIEW	WQFN	RUM	16	3000	Non-RoHS & Non-Green	Call TI	Call TI	-40 to 125		
TMUX6212PWR	ACTIVE	TSSOP	PW	16	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	X212	Samples
TMUX6212RUMR	PREVIEW	WQFN	RUM	16	3000	Non-RoHS & Non-Green	Call TI	Call TI	-40 to 125		
TMUX6213PWR	PREVIEW	TSSOP	PW	16	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	X213	
TMUX6213RUMR	PREVIEW	WQFN	RUM	16	3000	Non-RoHS & Non-Green	Call TI	Call TI	-40 to 125		

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

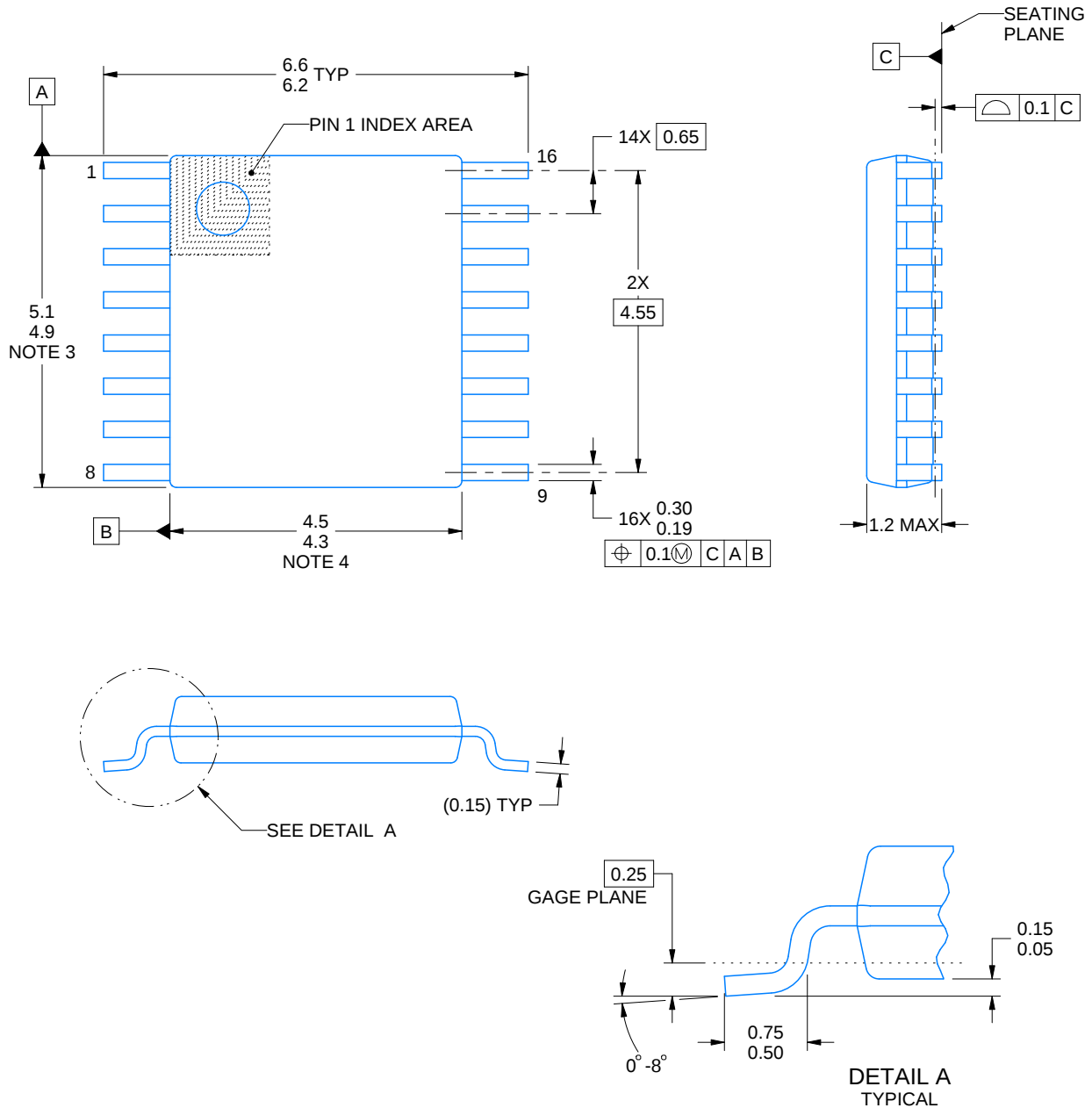
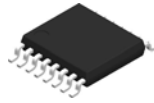
(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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NOTES:

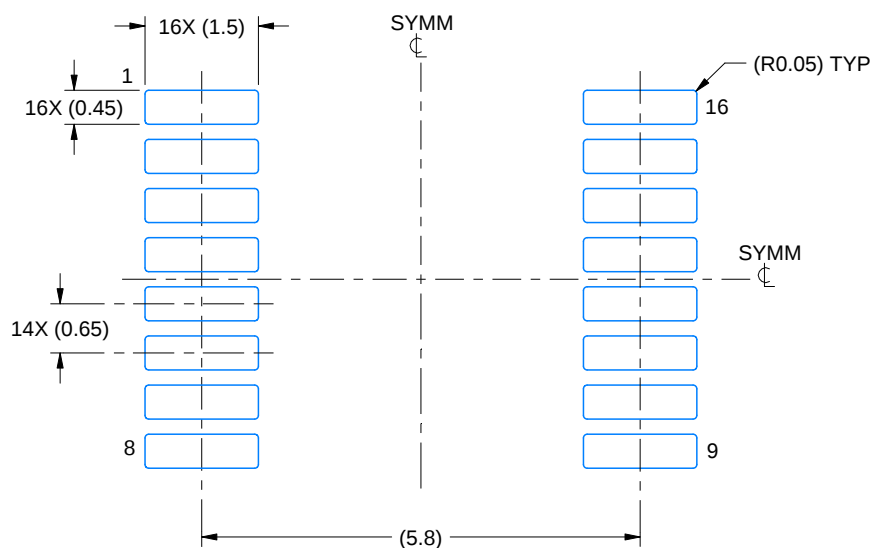
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
5. Reference JEDEC registration MO-153.

EXAMPLE BOARD LAYOUT

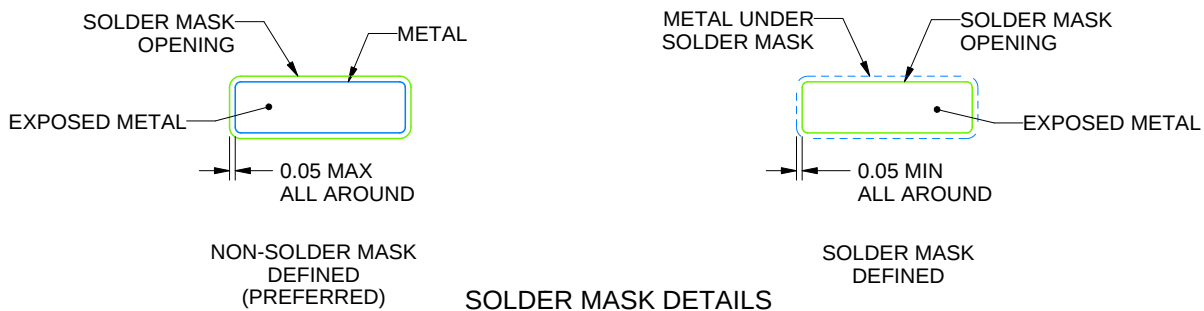
PW0016A

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 10X



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NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

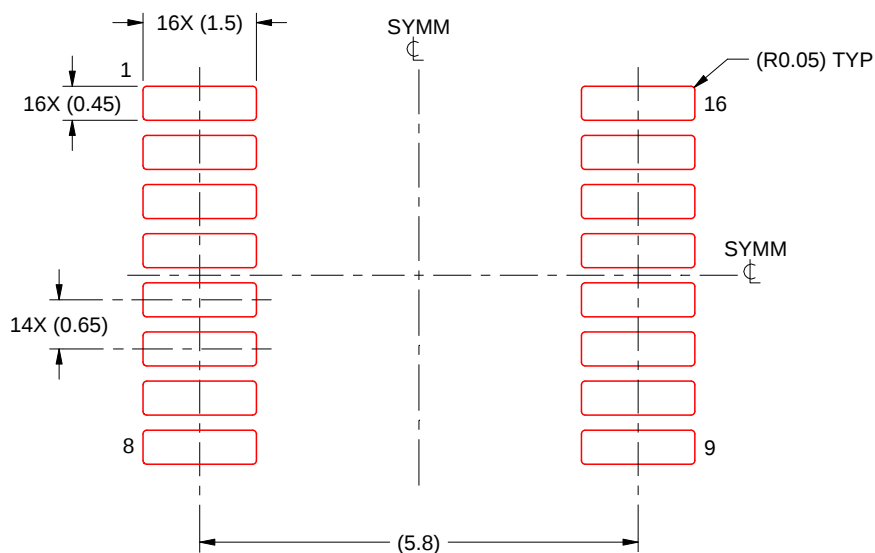
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

PW0016A

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE: 10X

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NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

重要声明和免责声明

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